1. General description

Hyperfast power diode in a 2-lead TO220 plastic package.

2. Features and benefits

- · Low reverse recovery current and low thermal resistance
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies
- · Half-bridge lighting ballasts

BYC8-600

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 109 °C; square-wave pulse; Fig. 1; Fig. 2	-	-	8	Α
Static characte	eristics					
V_{F}	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	_	1.4	1.85	V
Dynamic chara	acteristics					
t _{rr}	reverse recovery time	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$	-	19	-	ns

Hyperfast power diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A 001aaa020
2	Α	anode	}	001aaa020
mb	mb	mounting base; cathode	TO-220AC (SOD59)	

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC8-600	TO220	BYC8-600,127	Tube	50	SOD59	27-Nov-2012

Hyperfast power diode

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 109 °C; square-wave pulse; Fig. 1; Fig. 2	-	8	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 109 °C; square-wave pulse	-	16	A
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse	-	80	Α
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	88	Α
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

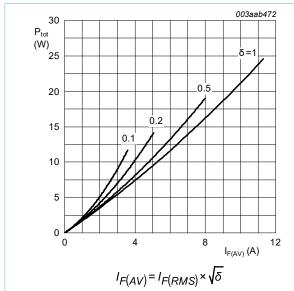


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

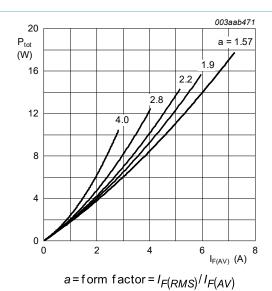


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

Hyperfast power diode

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 3	-	-	2.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air		-	60	-	K/W

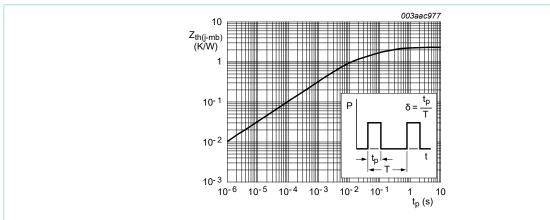


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

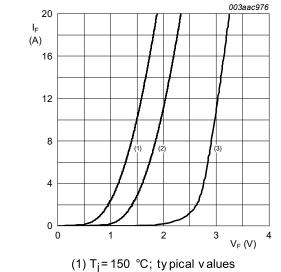
26 November 2019

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics				-	
V _F	forward voltage	I _F = 8 A; T _j = 25 °C	-	2	2.9	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.4	1.85	V
		I _F = 16 A; T _j = 150 °C	-	1.7	2.3	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	9	150	μA
		V _R = 600 V; T _j = 100 °C	-	1.1	3	mA
Dynamic ch	naracteristics		·			
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$	-	30	52	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$	-	19	-	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; Fig. 5$	-	32	40	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}$	-	1.5	5.5	А
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}$	-	9.5	12	А
Q _r	recovered charge	$I_F = 1 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}$	-	12	-	nC
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 100 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 6	-	8	10	V



(2) $T_j = 150$ °C; maximum values

(3) $T_i = 25$ °C; maximum values



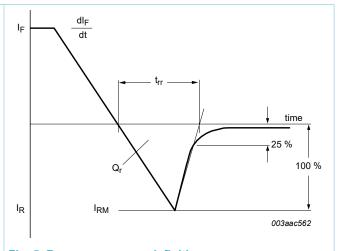
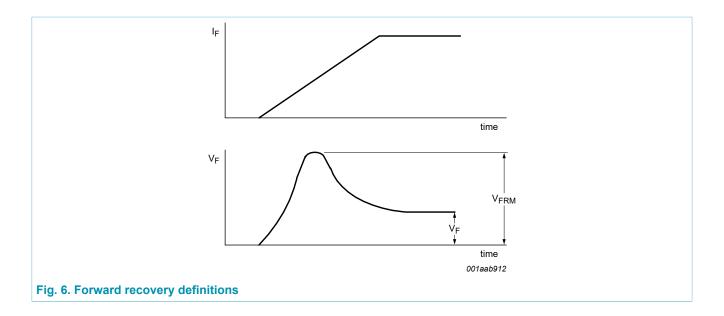


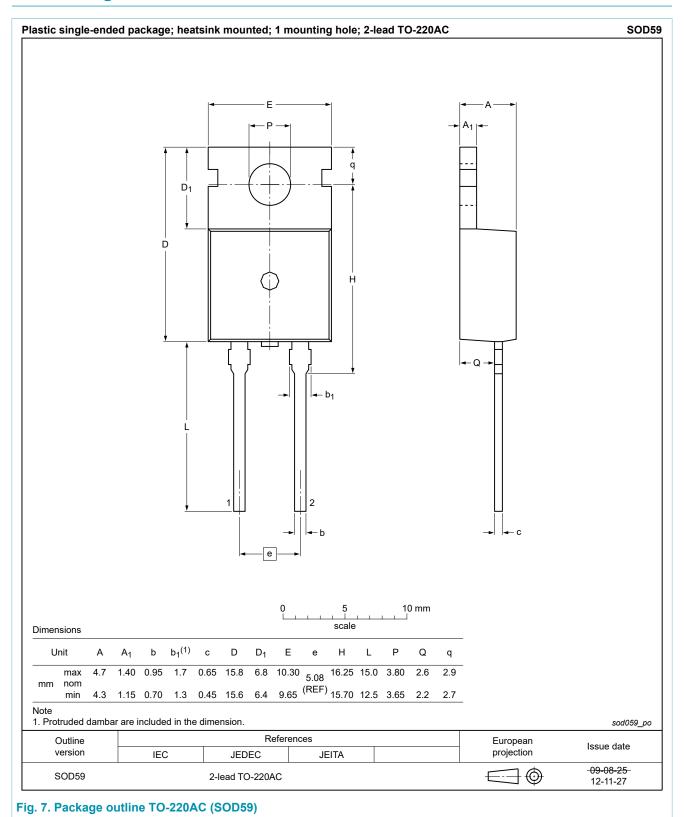
Fig. 5. Reverse recovery definitions; ramp recovery

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10. Package outline



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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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For more information, please visit: http://www.ween-semi.com
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